

4H 8inch N-Type SiC Ingot

属性 Property	単位Unit	量产级P	试片级D
晶型 Polytype		4H	
参杂剂 Dopant		n-type Nitrogen	
直径 Diameter	mm	200 ± 0.25	200 ± 0.25
厚度 Thickness	mm	≥10	
表面方向 Surface Orientation		4.0° toward < 11 ` 20 > ± 0.5°	4.0° toward < 11 ` 20 > ± 1°
电阻率 Resistivity	Ω·cm	0.018~0.025	0.010~0.030
主定位方向 Primary Flat Orientation		{10 10} ± 5.0°	{10 10} ± 5.0°
notch	mm	1-1.5	0.5-2
基面位错 BPD	cm ⁻²	<3000	
螺位错 TSD	cm ⁻²	<500	
多型的 Foreign Polytypes*		None	None, edge exclusion 5nm
多晶的 Polycrystal*		None	None, edge exclusion 5nm
微管密度 Micropipe Density	cm ⁻²	≤0.5	≤50
裂纹 Cracks*	number	None	None, edge exclusion 5nm
边缘缺陷 Edge Chips	number	None	2allowed, <
可见划痕 Visible Scratch#	mm	None	
*Defects limits apply to entire wafer surface except for the edge exclusion area.			
#The defects should be checked on Si face only.			
Product with other specifications can be customized.			